

## ABSTRACT

A method of making tungsten plug of integrated circuit is disclosed. The present invention is structured to deposit W metal by CVD onto the wafer which has Ti/TiN sputtered on as its top layer by employing quartz clamp rings of different sizes in two CVD chambers. The method can eliminate the Volcano phenomena in Ti, TiN or W metals and prevent peeling.

666020-00464260  
CIP.04.wpd